VS-ST280CH Series

Vishay Semiconductors



Phase Control Thyristors (Hockey PUK Version), 500 A



A-PUK (TO-200AB)

PRIMARY CHARACTERISTICS					
I _{T(AV)}	500 A				
V _{DRM} /V _{RRM}	400 V, 600 V				
V _{TM}	1.35 V				
I _{GT}	90 mA				
TJ	-40 °C to +150 °C				
Package	A-PUK (TO-200AB)				
Circuit configuration	Single SCR				

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-PUK (TO-200AB)
- Extended temperature range
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
		500	A				
I _{T(AV)}	T _{hs}	80	۵°				
1		1130	A				
I _{T(RMS)}	T _{hs}	25	°C				
1	50 Hz	7200	۵				
ITSM	60 Hz	7500	A				
l ² t	50 Hz	260	kA ² s				
1-1	60 Hz	230	KA-S				
V _{DRM} /V _{RRM}		400 to 600	V				
t _q	Typical	100	μs				
TJ		-40 to 150	۵°				

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I _{DRM} /I _{RRM} MAXIMUM AT T _J = T _J MAXIMUM MA					
VS-ST280CHC	04	400	500	75					
V3-31200CHC	06	600	700	15					

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ABSOLUTE MAXIMUM RATING	S					
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current	1	180° condu	ction, half sine v	wave	500 (185)	А
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	80 (110)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink temp	erature double side cooled	1130	
		t = 10 ms	No voltage		7200	
Maximum peak, one-cycle	l=o	t = 8.3 ms	reapplied		7500	Α
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		6000	kA ² s
		t = 8.3 ms	reapplied	Sinusoidal half wave,	6300	
	l ² t	t = 10 ms	No voltage reapplied 100 % V _{RRM}	initial $T_J = T_J$ maximum	260	
Maximum I ² t for fusing		t = 8.3 ms			235	
Maximum r tior rusing	11	t = 10 ms			180	
		t = 8.3 ms	reapplied		165	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10) ms, no voltage	e reapplied	2600	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x \mid_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.84	v
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T _J = T _J maximum			mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			0.47	1115.2
Maximum on-state voltage	V_{TM}	I_{pk} = 1000 A, T_J = T_J maximum, t_p = 10 ms sine pulse			1.35	V
Maximum holding current	Ι _Η	T 25 °C	anodo supply 1	2 V resistive lead	600	mA
Maximum (typical) latching current	١L	$1_{\rm J} = 25$ C,	anoue supply 1	2 V resistive load	1000 (300)	IIIA

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \leq 1 \; \mu s$ $T_J = T_J$ maximum, anode voltage $\leq 80 \; \% \; V_{DRM}$	1000	A/µs			
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/µs V _d 0.67 % V _{DRM} , T _J = 25 °C	1.0				
Typical turn-off time	tq	I_{TM} = 300 A, T_J = T_J maximum, dl/dt = 20 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	100	μs			

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNIT S			
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs			
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	75	mA			

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TRIGGERING							
PARAMETER	SYMBOL	те	ST CONDITIONS	VAL	UNITS		
FANAIMETEN	STINIBUL	16	STCONDITIONS	TYP.	MAX.		
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10).0	W	
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv	
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 ms$	3	.0	А	
Maximum peak positive gate voltage	+ V _{GM}		+ < 5 mg	2	0	V	
Maximum peak negative gate voltage	- V _{GM}	ij = ij maximum,	haximum, $t_p \le 5 \text{ ms}$ 5.0		.0	v	
		T _J = - 40 °C		180	-		
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger/ current/voltage are the lowest	90	150	mA	
		T _J = 150 °C		30	-		
		T _J = - 40 °C	value which will trigger all units	2.9	-		
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	12 V anode to cathode applied	1.8	3.0	V	
		T _J = 150 °C		1.0	-		
DC gate current not to trigger	I _{GD}	T. T. movimum	Maximum gate current/voltage not to trigger is the maximum	1	0	mA	
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.30		V	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum operating junction and storage temperature range	T _J , T _{Stg}		- 40 to 150	°C			
Maximum thermal resistance,	Р	DC operation single side cooled	0.17				
junction to heatsink		DC operation double side cooled	0.08	K/W			
Maximum thermal resistance,	P	DC operation single side cooled	0.033	r∨ vv			
case to heatsink	R _{thC-hs}	DC operation double side cooled	0.017				
Mounting force, ± 10 %			4900 (500)	N (kg)			
Approximate weight			50	g			
Case style		See dimensions - link at the end of datasheet A-PUK (TO-200A		200AB)			

$\Delta \mathbf{R}_{thJ-hs}$ CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULAR	R CONDUCTION	TEAT CONDITIONS	UNITS
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS
180°	0.016	0.017	0.011	0.011		
120°	0.019	0.019	0.019	0.019		
90°	0.024	0.024	0.026	0.026	$T_J = T_J maximum$	K/W
60°	0.035	0.035	0.036	0.037		
30°	0.060	0.060	0.060	0.061		

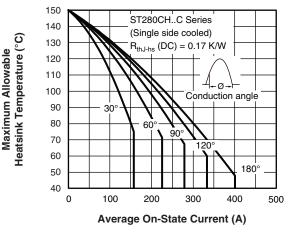
Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

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Fig. 1 - Current Ratings Characteristics

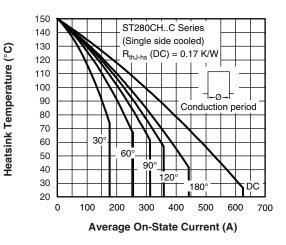


Fig. 2 - Current Ratings Characteristics



Maximum Allowable

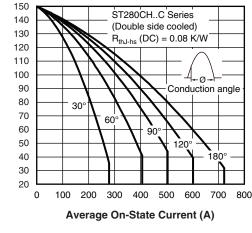
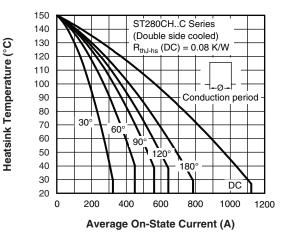


Fig. 3 - Current Ratings Characteristics



Maximum Allowable

Maximum Average

Fig. 4 - Current Ratings Characteristics

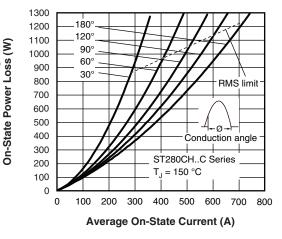


Fig. 5 - On-State Power Loss Characteristics

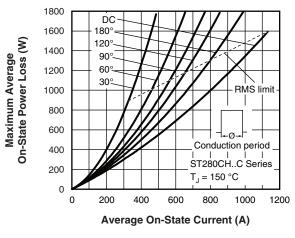


Fig. 6 - On-State Power Loss Characteristics

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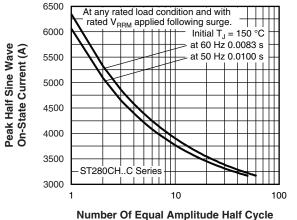
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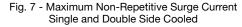
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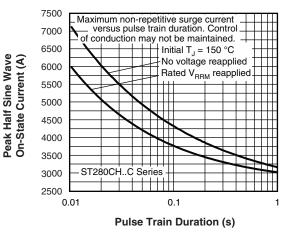


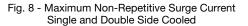


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Number Of Equal Amplitude Half Cycle Current Pulses (N)







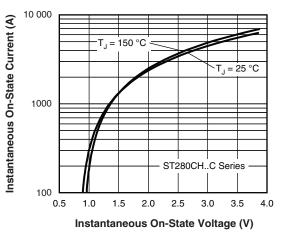
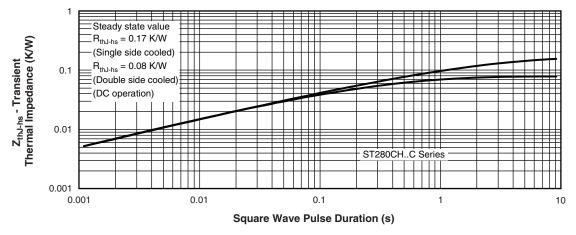


Fig. 9 - On-State Voltage Drop Characteristics





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VS-ST280CH Series SHA www.vishay.com **Vishay Semiconductors** 100 Rectangular gate pulse a) Recommended load line for rated dl/dt: 20 V, 10 Ω ; t_r \leq 1 μ s (1) $P_{GM} = 10 W$, $t_p = 4 \text{ ms}$ Instantaneous Gate Voltage (V) (2) $P_{GM} = 20 W$, $t_p^{\nu} = 2 \text{ ms}$ t_p = 1 ms (3) $P_{GM} = 40 \text{ W},$ $t_{p}^{\prime} = 0.66 \text{ ms}$ b) Recommended load line for -(4) $P_{GM} = 60 W$, \leq 30 % rated dl/dt: 10 V, 10 Ω 1 10 'a' t,≤1µs ≡ (b) ш 11 40 1 25 റ് റ് (2) 50 (1)V_{GD} + പ് Frequency limited by PG(AV) I_{GD} Device: ST280CH..C Series 0.1 0.01 0.001 0.1 1 10 100 Instantaneous Gate Current (A)

Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	ST	28	0	СН	06	с	1	-	
		2	3	4	5	6	7	8	9	
	 Vishay Semiconductors product Thyristor Essential part number 0 = converter grade CH = ceramic PUK, high temperature Voltage code x 100 = V_{RRM} (see Voltage Ratings table) 									
	7 - 8 -		C = PUK case A-PUK (TO-200AB) 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)							
	9 -	2 = 3 =	eyelet t fast-on	erminals termina dt: ● No	s (gate a	and auxi and aux 0 V/µs	iliary cat kiliary ca (standa	thode so athode s rd selec		ads)

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95074				



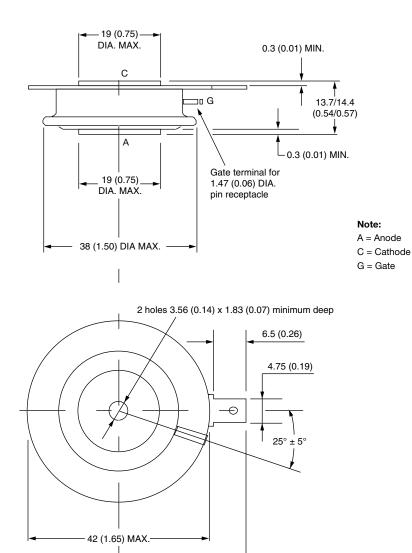


A-PUK (TO-200AB)

DIMENSIONS in millimeters (inches)

Anode to gate

Creepage distance: 7.62 (0.30) minimum Strike distance: 7.12 (0.28) minimum



◄ 28 (1.10) →

Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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